Respectfully submitted,

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APPENDIX A -Claim Amendments

Please amend claims 3, 5 and 7 in accordance with the following instructions.

A1

3.(Amended) A method according to claim 1 [or 2] wherein said copper ions are copper (I) ions.

A2

5.(Amended) A method according to any of [claims 1 to 4] claim 1 further comprising the step of subjecting the mixture formed by said precipitation step to a diafiltration and/or ultrafiltration treatment.

A3

7.(Amended) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to [any of the previous claims] claim 1.

Please enter claims 8-29 as indicated.

A4

8.(New) A method according to claim 2 wherein said copper ions are copper (I) ions.

9.(New) A method according to claim 8 wherein said copper (I) ions are incorporated as copper (I) chloride.

10.(New) A method according to any of claim 2 further comprising the step of subjecting the mixture formed by said precipitation step to a diafiltration and/or ultrafiltration treatment.

11.(New) A method according to claim 10 wherein said diafiltration and/or ultrafiltration treatment is performed in the presence of a compound preventing agglomeration of said ZnS:Cu particles.

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12.(New) A method according to any of claim 3 further comprising the step of subjecting the mixture formed by said precipitation step to a diafiltration and/or ultrafiltration treatment.

13.(New) A method according to claim 12 wherein said diafiltration and/or ultrafiltration treatment is performed in the presence of a compound preventing agglomeration of said ZnS:Cu particles.

14.(New) A method according to any of claim 4 further comprising the step of subjecting the mixture formed by said precipitation step to a diafiltration and/or ultrafiltration treatment.

15.(New) A method according to claim 14 wherein said diafiltration and/or ultrafiltration treatment is performed in the presence of a compound preventing agglomeration of said ZnS:Cu particles.

16.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 2.

17.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 3.

18.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 4.

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19.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 5.

20.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 6.

21.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 7.

22.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 8.

23.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 9.

24.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 10.

25.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 11.

26.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 12.

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27.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 13.

28.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 14.

29.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 15.